650V 50A Field Stop Trench IGBT

Datasheet

# **ROHM**

V <sub>CES</sub>	650V
I <sub>C(100°C)</sub>	50A
V <sub>CE(sat) (Typ.)</sub>	1.6V
$P_D$	277W

#### Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Built in Very Fast & Soft Recovery FRD (RFN - Series)
- 5) Pb free Lead Plating; RoHS Compliant

#### Applications

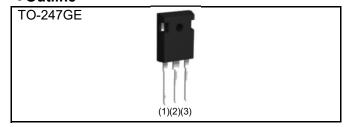
**PFC** 

**UPS** 

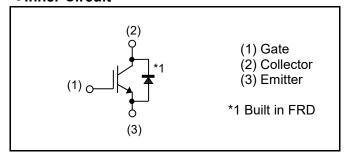
**Power Conditioner** 

ΙH

#### Outline



#### ●Inner Circuit



Packaging Specifications

		Packaging	Tube	
		Reel Size (mm)	-	
	Typo	Tape Width (mm)	-	
	Туре	Basic Ordering Unit (pcs)	600	
		Packing code	C13	
		Marking	RGTH00TS65D	

## ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit	
Collector - Emitter Voltage		V <sub>CES</sub>	650	V	
Gate - Emitter Voltage		V <sub>GES</sub>	±30	V	
0.11.4.0	T <sub>C</sub> = 25°C	I <sub>C</sub>	85	А	
Collector Current	T <sub>C</sub> = 100°C	I <sub>C</sub>	50	А	
Pulsed Collector Current		I <sub>CP</sub> *1	200	А	
Diode Forward Current	T <sub>C</sub> = 25°C	I <sub>F</sub>	50	А	
	T <sub>C</sub> = 100°C	I <sub>F</sub>	30	А	
Diode Pulsed Forward Current		I <sub>FP</sub> *1	200	А	
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>D</sub>	277	W	
	T <sub>C</sub> = 100°C	P <sub>D</sub>	138	W	
Operating Junction Temperature		Tj	-40 to +175	°C	
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C	

<sup>\*1</sup> Pulse width limited by T<sub>jmax.</sub>

#### ●Thermal Resistance

Parameter	Symbol	Values			Unit
raiailletei		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.54	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j-c)}$	-	-	1.42	°C/W

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
r al allielei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	-	-	V
Collector Cut - off Current	I <sub>CES</sub>	$V_{CE} = 650V, V_{GE} = 0V$	-	-	10	μΑ
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V, V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$V_{CE} = 5V, I_{C} = 34.7 \text{mA}$	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_C = 50A$ , $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	-	1.6 2.1	2.1 -	V

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Unit		
i didilicici			Min.	Тур.	Max.	Offic
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 30V	-	2740	-	
Output Capacitance	C <sub>oes</sub>	V <sub>GE</sub> = 0V	-	106	-	pF
Reverse Transfer Capacitance	C <sub>res</sub>	f = 1MHz	-	43	-	
Total Gate Charge	$Q_g$	V <sub>CE</sub> = 300V	-	94	-	
Gate - Emitter Charge	$Q_ge$	I <sub>C</sub> = 50A	-	22	-	nC
Gate - Collector Charge	$Q_{gc}$	V <sub>GE</sub> = 15V	-	31	-	
Turn - on Delay Time	t <sub>d(on)</sub>	I <sub>C</sub> = 50A, V <sub>CC</sub> = 400V	-	39	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	63	-	
Turn - off Delay Time	$t_{d(off)}$	T <sub>j</sub> = 25°C	-	143	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	50	-	
Turn - on Delay Time	t <sub>d(on)</sub>	I <sub>C</sub> = 50A, V <sub>CC</sub> = 400V	-	39	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	63	-	200
Turn - off Delay Time	$t_{d(off)}$	T <sub>j</sub> = 175°C	-	159	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	62	-	
		I <sub>C</sub> = 200A, V <sub>CC</sub> = 520V				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FULL SQUARE			-
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
raiailletei			Min.	Тур.	Max.	Offic
		I <sub>F</sub> = 30A				
Diode Forward Voltage	$V_{F}$	T <sub>j</sub> = 25°C	-	1.45	2.0	V
		T <sub>j</sub> = 175°C	-	1.25	1	
Diode Reverse Recovery Time	t <sub>rr</sub>	$I_F = 30A$ $V_{CC} = 400V$ $di_F/dt = 200A/\mu s$ $T_j = 25^{\circ}C$	-	54	-	ns
Diode Peak Reverse Recovery Current	I <sub>rr</sub>		-	7.4	1	A
Diode Reverse Recovery Charge	$Q_{rr}$		-	0.22	-	μC
Diode Reverse Recovery Time	t <sub>rr</sub>	$I_F = 30A$ $V_{CC} = 400V$ $di_F/dt = 200A/\mu s$ $T_j = 175^{\circ}C$	-	225	-	ns
Diode Peak Reverse Recovery Current	l <sub>rr</sub>		-	12.8	1	Α
Diode Reverse Recovery Charge	$Q_{rr}$		-	1.60	-	μC

Fig.1 Power Dissipation vs. Case Temperature

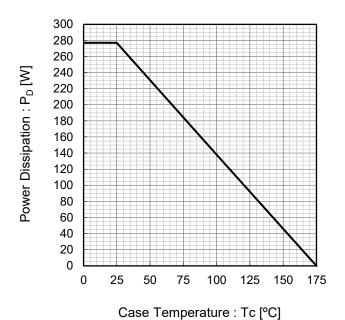


Fig.2 Collector Current vs. Case Temperature

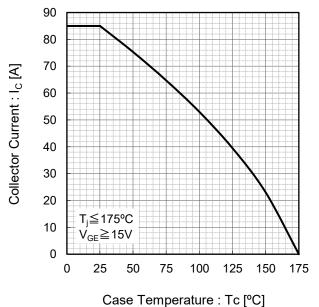


Fig.3 Forward Bias Safe Operating Area

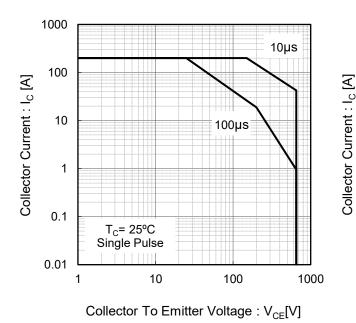
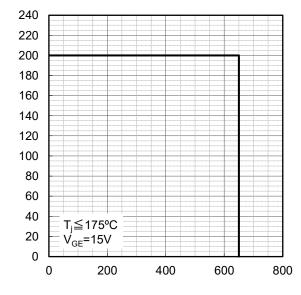


Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage : V<sub>CE</sub>[V]

Fig.5 Typical Output Characteristics

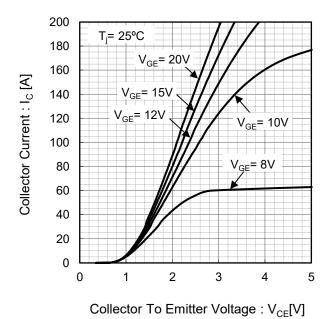
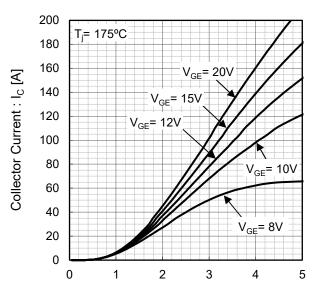


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : V<sub>CE</sub>[V]

Fig.7 Typical Transfer Characteristics

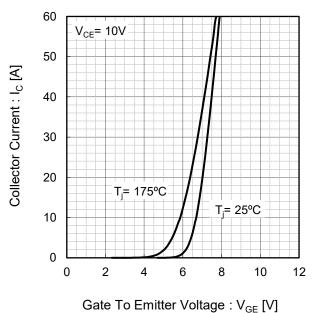
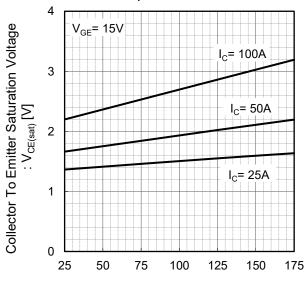
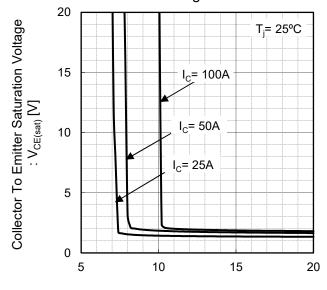


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



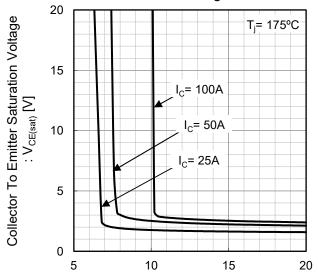
Junction Temperature : T<sub>i</sub> [°C]

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

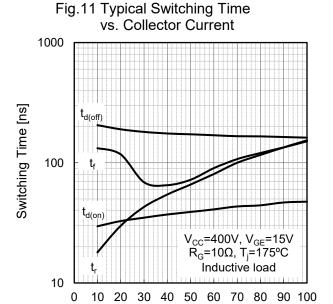


Gate To Emitter Voltage : V<sub>GE</sub> [V]

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : V<sub>GE</sub> [V]



Collector Current : I<sub>C</sub> [A]

Fig.12 Typical Switching Time vs. Gate Resistance

1000

td(off)

td(on)

Vcc=400V, Ic=50A
VGE=15V, Tj=175°C
Inductive load

10

10

10

20

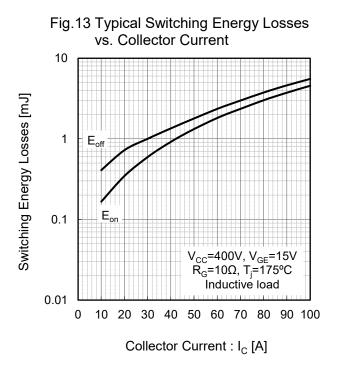
30

40

50

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Gate Resistance :  $R_G[\Omega]$ 



vs. Gate Resistance 10 Switching Energy Losses [mJ]  $\mathsf{E}_{\mathsf{off}}$ 1  $E_{on}$ 0.1 V<sub>CC</sub>=400V, I<sub>C</sub>=50A V<sub>GE</sub>=15V, T<sub>j</sub>=175°C Inductive load 0.01 10 0 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz V<sub>GE</sub>=0V T<sub>i</sub>=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage :  $V_{CE}[V]$ 

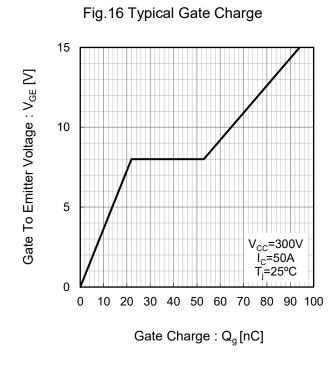


Fig.17 Typical Diode Forward Current vs. Forward Voltage 200 180 160 Forward Current: I<sub>F</sub> [A] 140 120 100 80 60 T<sub>i</sub>= 175°C 40 T<sub>i</sub>= 25°C 20 0 1.5 2.5 3.5 0 0.5 2 3 Forward Voltage : V<sub>F</sub>[V]

Fig.18 Typical Diode Reverse Recovery Time vs. Forward Current 400 V<sub>CC</sub>=400V di<sub>F</sub>/dt=200A/μs Reverse Recovery Time : t<sub>rr</sub> [ns] Inductive load 300 T<sub>i</sub>= 175°C 200 100 T<sub>i</sub>= 25°C 0 0 10 20 30 40 50 Forward Current : I<sub>F</sub> [A]

Fig.19 Typical Diode Reverse Recovery Current vs. Forward Current

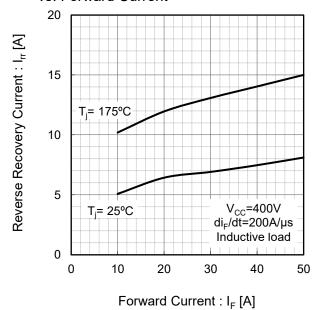
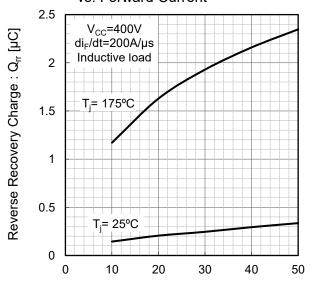


Fig.20 Typical Diode Reverse Recovery Charge vs. Forward Current



Forward Current : I<sub>F</sub> [A]

Fig.21 IGBT Transient Thermal Impedance

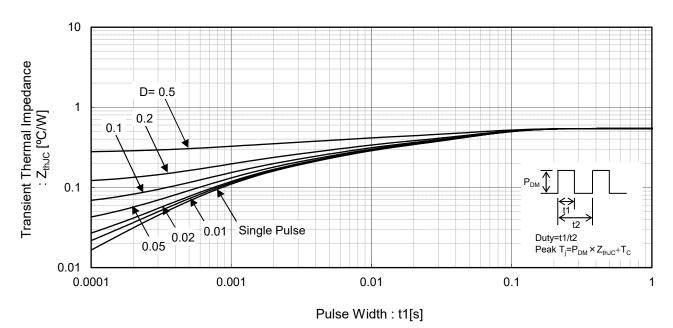
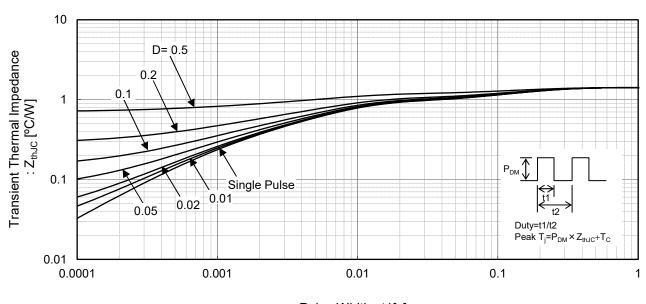


Fig.22 Diode Transient Thermal Impedance



### ●Inductive Load Switching Circuit and Waveform

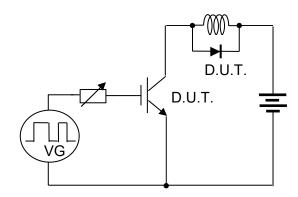


Fig.23 Inductive Load Circuit

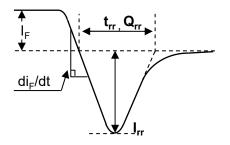


Fig.25 Diode Reverce Recovery Waveform

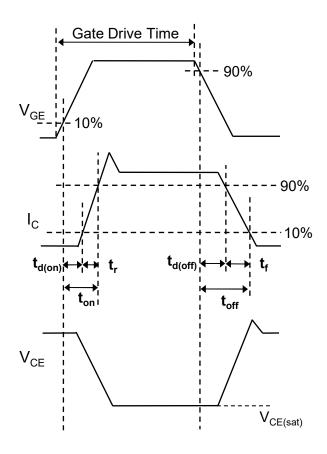


Fig.24 Inductive Load Waveform

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